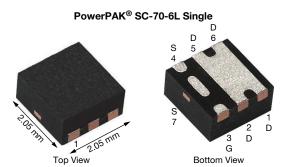


# N-Channel 80 V (D-S) MOSFET



PRODUCT SUMMARY									
V <sub>DS</sub> (V)	80								
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 10 \text{ V}$	0.038								
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 7.5 \text{ V}$	0.046								
Q <sub>g</sub> typ. (nC)	7.1								
I <sub>D</sub> (A) <sup>a</sup>	12								
Configuration	Single								

#### **FEATURES**

- TrenchFET® Gen IV power MOSFET
- Tuned for the lowest R<sub>DS</sub> x Q<sub>oss</sub>
- 100% R<sub>q</sub> and UIS tested
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912

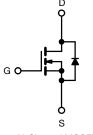


ROHS

HALOGEN FREE

#### **APPLICATIONS**

- Primary side switch
- DC/DC converter
- Motor drive switch
- Boost converter
- LED backlighting



N-Channel MOSFET

ORDERING INFORMATION							
Package	PowerPAK SC-70						
Lead (Pb)-free and halogen-free	SiA108DJ-T1-GE3						

ABSOLUTE MAXIMUM RATING	<b>iS</b> (T <sub>A</sub> = 25 °C, ι	ınless otherv	vise noted)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V <sub>DS</sub>	80	V
Gate-source voltage		$V_{GS}$	± 20	V
	T <sub>C</sub> = 25 °C		12 <sup>a</sup>	
0 1: 1 : 1 (T 150 00)	T <sub>C</sub> = 70 °C	1 . [	12 <sup>a</sup>	
Continuous drain current (T <sub>J</sub> = 150 °C)	T <sub>A</sub> =25 °C	l <sub>D</sub>	6.6 <sup>b, c</sup>	
	T <sub>A</sub> = 70 °C	1 [	5.3 b, c	A
Pulsed drain current (t = 100 μs)	•	I <sub>DM</sub>	30	^
Cartino and desirable account	T <sub>C</sub> = 25 °C	,	12 <sup>a</sup>	
Continuous source-drain diode current	T <sub>A</sub> = 70 °C	l <sub>S</sub>	2.9 b, c	
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	12	
Single pulse avalanche energy	L=0.1 mn	E <sub>AS</sub>	7.2	mJ
	T <sub>C</sub> = 25 °C		19	
Maximum navvar dissination	T <sub>C</sub> = 70 °C	T _ [	12	W
Maximum power dissipation	T <sub>A</sub> = 25 °C	P <sub>D</sub>	3.5 b, c	VV
	T <sub>A</sub> = 70 °C	Ī [	2.2 b, c	
Operating junction and storage temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C	
Soldering recommendations (peak tempera	ture) <sup>d, e</sup>		260	

THERMAL RESISTANCE RATINGS									
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT				
Maximum junction-to-ambient b, f	t ≤ 5 s	R <sub>thJA</sub>	28	36	°C/W				
Maximum junction-to-case (drain)	Steady state	$R_{thJC}$	5.3	6.5	C/VV				

#### Notes

- a. Package limited
- b. Surface mounted on 1" x 1" FR4 board
- c. t = 5 s
- d. See solder profile (<a href="https://www.vishay.com/doc?73257">www.vishay.com/doc?73257</a>). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- f. Maximum under steady state conditions is 80 °C/W



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# Vishay Siliconix

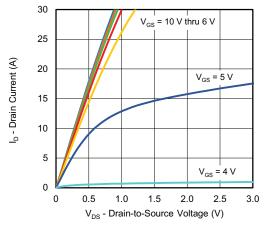
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static					•	•
Drain-source breakdown voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	80	-	-	V
V <sub>DS</sub> temperature coefficient	$\Delta V_{DS}/T_{J}$	I <sub>D</sub> = 250 μA	-	60	-	
V <sub>GS(th)</sub> temperature coefficient	ΔV <sub>GS(th)</sub> /T <sub>J</sub>	I <sub>D</sub> = 250 μA	-	-6.8	-	mV/°C
Gate-source threshold voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2	-	4	V
Gate-source leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	100	nA
Zava mata valtama duain avuunnt		V <sub>DS</sub> = 80 V, V <sub>GS</sub> = 0 V	-	-	1	
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 80 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 70 °C	-	-	10	μA
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	10	-	-	Α
Drain aguras en etata registance 3	В	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 4 A	-	0.032	0.038	
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 7.5 V, I <sub>D</sub> = 2 A	-	0.034	0.046	Ω
Forward transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 15 A	-	28	-	S
Dynamic <sup>b</sup>						
Input capacitance	C <sub>iss</sub>		-	545	-	
Output capacitance	C <sub>oss</sub>	$V_{DS} = 40 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	75	-	pF
Reverse transfer capacitance	C <sub>rss</sub>		-	9	-	
Tatal sate about	0	V <sub>DS</sub> = 40 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 4 A	-	9.2	13	nC
Total gate charge	Qg		-	7.1	10	
Gate-source charge	Q <sub>gs</sub>	$V_{DS} = 40 \text{ V}, V_{GS} = 7.5 \text{ V}, I_D = 4 \text{ A}$	-	2.8	-	
Gate-drain charge	Q <sub>gd</sub>		-	1.7	-	
Output charge	Q <sub>oss</sub>	V <sub>DS</sub> = 40 V, V <sub>GS</sub> = 0 V	-	9	-	
Gate resistance	R <sub>q</sub>	f = 1 MHz	0.3	1.3	2.6	Ω
Turn-on delay time	t <sub>d(on)</sub>		-	10	20	
Rise time	t <sub>r</sub>	$V_{DD} = 40 \text{ V}, R_L = 10 \Omega, I_D \cong 4 \text{ A},$	-	5	10	
Turn-off delay time	t <sub>d(off)</sub>	$V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	14	30	1
Fall time	t <sub>f</sub>		-	5	10	1
Turn-on delay time	t <sub>d(on)</sub>		-	11	20	ns ns
Rise time	t <sub>r</sub>	$V_{DD} = 40 \text{ V}, R_L = 10 \Omega, I_D \cong 4 \text{ A},$	-	5	10	
Turn-off delay time	t <sub>d(off)</sub>	$V_{GEN} = 7.5 \text{ V}, R_g = 1 \Omega$	-	12	25	
Fall time	3(0.1)					Ī
<b>Drain-Source Body Diode Characteristi</b>	cs				•	
Continuous source-drain diode current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	-	-	12	
Pulse diode forward current	I <sub>SM</sub>		-	-	30	A
Body diode voltage	V <sub>SD</sub>	I <sub>S</sub> = 4 A, V <sub>GS</sub> = 0 V	-	0.82	1.2	V
Body diode reverse recovery time	t <sub>rr</sub>	- <del></del>	-	30	60	ns
Body diode reverse recovery charge	Q <sub>rr</sub>	$I_F = 4 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s},$	-	25	50	nC
Reverse recovery fall time	t <sub>a</sub>	$T_J = 25  ^{\circ}\text{C}$	-	20	-	
Reverse recovery rise time	t <sub>b</sub>		_	10	_	ns

#### **Notes**

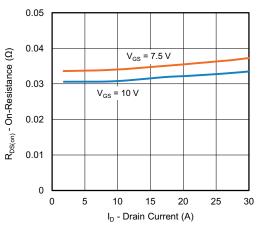
- a. Pulse test: pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %
- b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

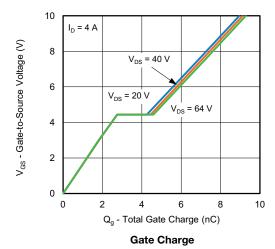


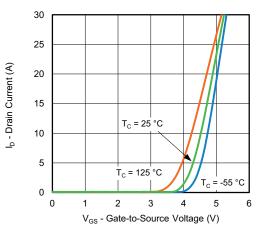


#### **Output Characteristics**

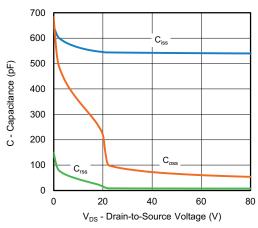


On-Resistance vs. Drain Current and Gate Voltage

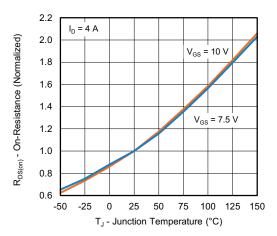




**Transfer Characteristics** 

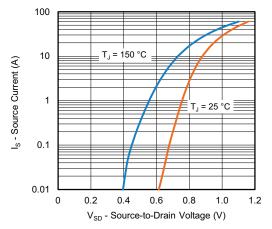


Capacitance

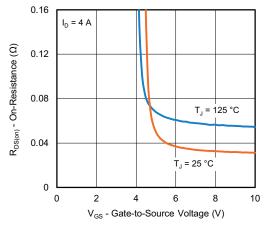


On-Resistance vs. Junction Temperature

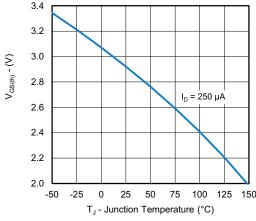




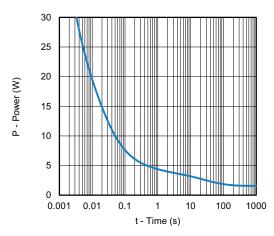
Source-Drain Diode Forward Voltage



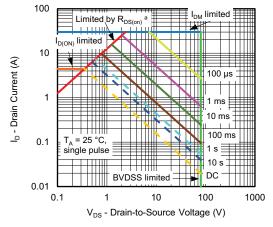
On-Resistance vs. Gate-to-Source Voltage



**Threshold Voltage** 



Single Pulse Power, Junction-to-Ambient

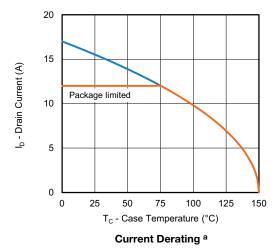


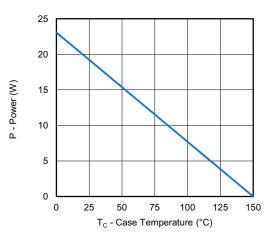
Safe Operating Area, Junction-to-Ambient

## Note

a.  $V_{GS}$  > minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified





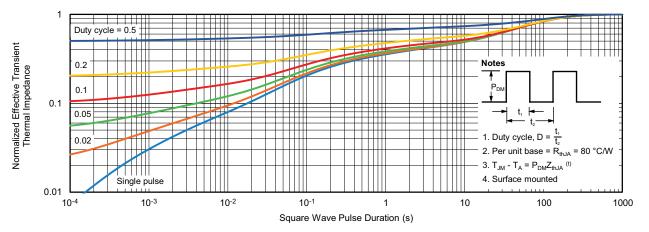


Power, Junction-to-Case

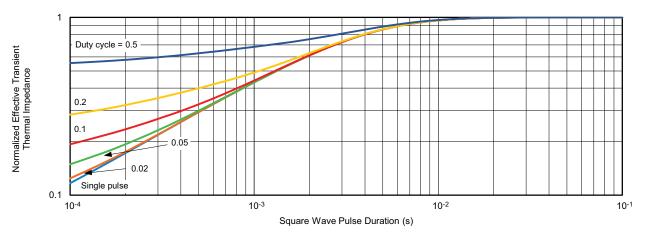
#### Note

a. The power dissipation P<sub>D</sub> is based on T<sub>J</sub> max. = 25 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit





Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?77827">www.vishay.com/ppg?77827</a>.





Vishay Siliconix

# PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
  Package outline exclusive of mold flash and metal burr
  Package outline inclusive of plating

			SINGL	_E PAD			DUAL PAD						
DIM	M	ILLIMETER	RS		INCHES		M	ILLIMETER	RS		INCHES		
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032	
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002	
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015	
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010	
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085	
D1	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028	
D2	0.135	0.235	0.335	0.005	0.009	0.013							
Е	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085	
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041	
E2	0.345	0.395	0.445	0.014	0.016	0.018							
E3	0.425	0.475	0.525	0.017	0.019	0.021							
е		0.65 BSC			0.026 BSC	,	0.65 BSC			0.026 BSC			
K		0.275 TYP	1		0.011 TYP		0.275 TYP			0.011 TYP			
K1		0.400 TYP	1		0.016 TYP			0.320 TYP			0.013 TYP		
K2		0.240 TYP	1		0.009 TYP			0.252 TYP			0.010 TYP		
К3		0.225 TYP	1	0.009 TYP									
K4		0.355 TYP	1		0.014 TYP								
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015	
Т							0.05	0.10	0.15	0.002	0.004	0.006	
ECNI- C C	7404 D	. 0 00 1	. 07										

ECN: C-07431 - Rev. C, 06-Aug-07

DWG: 5934

Document Number: 73001 06-Aug-07



# RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Single



Dimensions in mm/(Inches)

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ATTLICATION NOT



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Vishay

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